High-speed switching diodes Rev. 05 — 25 August 2008

Product data sheet

1. Product profile

1.1 General description

High-speed switching diodes, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			Configuration	Package
	NXP	JEITA	JEDEC		configuration
BAS16	SOT23	-	TO-236AB	single	small
BAS16H	SOD123F	-	-	single	small and flat lead
BAS16J	SOD323F	SC-90	-	single	very small and flat lead
BAS16L	SOD882	-	-	single	leadless ultra small
BAS16T	SOT416	SC-75	-	single	ultra small
BAS16VV	SOT666	-	-	triple isolated	ultra small and flat lead
BAS16VY	SOT363	SC-88	-	triple isolated	very small
BAS16W	SOT323	SC-70	-	single	very small
BAS316	SOD323	SC-76	-	single	very small
BAS516	SOD523	SC-79	-	single	ultra small and flat lead

1.2 Features

- High switching speed: $t_{rr} \le 4$ ns
- Low leakage current
- Repetitive peak reverse voltage: $V_{RRM} \le 100 \text{ V}$

1.3 Applications

- High-speed switching
- General-purpose switching

- Low capacitance
- Reverse voltage: V_R ≤ 100 V
- Small SMD plastic packages



High-speed switching diodes

1.4 Quick reference data

Table 2.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode)					
V _R	reverse voltage		-	-	100	V
I _R	reverse current	V _R = 80 V	-	-	0.5	μA
t _{rr}	reverse recovery time		<u>[1]</u> _	-	4	ns

[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

2. Pinning information

Pin	Description	Simplified outline	Graphic symbol
BAS16;	BAS16T; BAS16W		
1	anode		_
2	not connected	3	3
3	cathode	1 2 006aaa144	1 <u>2</u> 006aaa764
	; BAS16J; BAS316; BAS516		
1	cathode	<u>[1]</u>	
2	anode	1 2 001aab540	1 2 006aab040
BAS16L			
1	cathode	[1]	
2	anode	1 2 Transparent top view	1 2 006aab040
BAS16V	V; BAS16VY		
1	anode (diode 1)		
2	anode (diode 2)	6 5 4	6 5 4
3	anode (diode 3)		
4	cathode (diode 3)		
5	cathode (diode 2)		0
6	cathode (diode 1)	001aab555	1 2 3 006aab10

[1] The marking bar indicates the cathode.

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3. Ordering information

Table 4. Orde	ring inform	ation	
Type number	Package		
	Name	Description	Version
BAS16	-	plastic surface-mounted package; 3 leads	SOT23
BAS16H	-	plastic surface-mounted package; 2 leads	SOD123F
BAS16J	SC-90	plastic surface-mounted package; 2 leads	SOD323F
BAS16L	-	leadless ultra small plastic package; 2 terminals; body 1.0 \times 0.6 \times 0.5 mm	SOD882
BAS16T	SC-75	plastic surface-mounted package; 3 leads	SOT416
BAS16VV	-	plastic surface-mounted package; 6 leads	SOT666
BAS16VY	SC-88	plastic surface-mounted package; 6 leads	SOT363
BAS16W	SC-70	plastic surface-mounted package; 3 leads	SOT323
BAS316	SC-76	plastic surface-mounted package; 2 leads	SOD323
BAS516	SC-79	plastic surface-mounted package; 2 leads	SOD523

4. Marking

Table 5.Marking codes	
Type number	Marking code ^[1]
BAS16	A6*
BAS16H	A1
BAS16J	AR
BAS16L	S2
BAS16T	A6
BAS16VV	53
BAS16VY	16*
BAS16W	A6*
BAS316	A6
BAS516	6

[1] * = -: made in Hong Kong

* = p: made in Hong Kong

* = t: made in Malaysia

* = W: made in China

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5. Limiting values

repetitive peak reverse voltage reverse voltage forward current BAS16 BAS16H BAS16L BAS16L BAS16T BAS16VV BAS16VV BAS16VY BAS16W		- [1] - [2] - [1] - [1][3] -	100 100 215 215 155	V V mA mA mA
voltage reverse voltage forward current BAS16 BAS16H BAS16L BAS16C BAS16VV BAS16VV		[1] - [2] - [1] -	100 215 215 155	V mA mA
forward current BAS16 BAS16H BAS16L BAS16T BAS16VV BAS16VV		[1] - [2] - [1] -	215 215 155	mA mA
BAS16 BAS16H BAS16L BAS16T BAS16VV BAS16VY		[2] - [1] -	215 155	mA
BAS16H BAS16L BAS16T BAS16VV BAS16VY		[2] - [1] -	215 155	mA
BAS16L BAS16T BAS16VV BAS16VY		<u>[1]</u> -	155	
BAS16VV BAS16VY				mA
BAS16VY		[1][3] _		
BAS16W			200	mA
2,101011		<u>[1]</u> -	175	mA
BAS16J BAS316 BAS516		<u>[1]</u> -	250	mA
repetitive peak forward current	$\begin{array}{l} t_p \leq 0.5 \ \mu s; \\ \delta \leq 0.25 \end{array}$	-	500	mA
non-repetitive peak forward	square wave	[4]		
current	$t_p = 1 \ \mu s$	-	4	А
	t _p = 1 ms	-	1	А
	t _p = 1 s	-	0.5	А
total power dissipation				
BAS16	$T_{amb} \le 25 \ ^{\circ}C$		250	mW
BAS16H	$T_{amb} \le 25 \ ^{\circ}C$	[2][5] _ [6]	380	mW
		[5][6] _ [7]	830	mW
BAS16J	$T_{amb} \leq 25 \ ^{\circ}C$	[5][6] [7]	550	mW
BAS16L	$T_{amb} \le 25 \ ^{\circ}C$	[2][5] _ [6]	250	mW
BAS16T	$T_{sp} \le 90 \ ^{\circ}C$	<u>[1]</u> _	170	mW
BAS16VV	$T_{amb} \leq 25 \ ^{\circ}C$	[1][3] [5][8]	180	mW
BAS16VY	$T_{sp} \leq 85 ~^{\circ}C$	[1][3] _ [8]	250	mW
BAS16W	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	200	mW
BAS316	$T_{sp} \le 90 \ ^{\circ}C$	[1][6] _	400	mW
	BAS16J BAS316 BAS516 repetitive peak forward current non-repetitive peak forward current total power dissipation BAS16 BAS16H BAS16H BAS16L BAS16L BAS16CV BAS16VV BAS16VV	$\begin{array}{c} BAS16J\\ BAS316\\ BAS316\\ BAS316\\ BAS316\\ BAS316\\ BAS316\\ \\ BAS316\\ \end{array} \qquad $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $	$\begin{array}{c c c c c c c c c c c c c c c c c c c $

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per device					
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB with 60 μ m copper strip line.

- [3] Single diode loaded.
- [4] $T_j = 25 \,^{\circ}C$ prior to surge.
- [5] Reflow soldering is the only recommended soldering method.
- [6] Soldering point of cathode tab.
- [7] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [8] Soldering points at pins 4, 5 and 6.

6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air			.76		
	BAS16		<u>[1]</u>	-	-	500	K/W
	BAS16H		[2][3]	-	-	330	K/W
			[3][4]	-	-	150	K/W
	BAS16J		[3][4]	-	-	230	K/W
	BAS16L		[2][3]	-	-	500	K/W
	BAS16VV		[2][3] [5]	-	-	700	K/W
			[3][4] [5]	-	-	410	K/W
	BAS16W		[1]	-	-	625	K/W
R _{th(j-t)}	thermal resistance from junction to tie-point						
	BAS16			-	-	330	K/W
	BAS16W			-	-	300	K/W

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Table 7.	Thermal characteristics continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point					
	BAS16H		<u>[6]</u> _	-	70	K/W
	BAS16J		<u>[6]</u> _	-	55	K/W
	BAS16T		-	-	350	K/W
	BAS16VY		[5][7] _	-	260	K/W
	BAS316		<u>[6]</u> _	-	150	K/W
	BAS516		<u>[6]</u> _	-	120	K/W

Table 7.	Thermal	characteristics	continue

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB with 60 μ m copper strip line.

- [3] Reflow soldering is the only recommended soldering method.
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².
- [5] Single diode loaded.
- Soldering point of cathode tab. [6]
- [7] Soldering points at pins 4, 5 and 6.

Characteristics 7.

Characteristics Table 8.

T_{amb} = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	•					
V _F	forward voltage		<u>[1]</u>			
		I _F = 1 mA	-	-	715	mV
		I _F = 10 mA	-	-	855	mV
		l _F = 50 mA	-	-	1	V
		l _F = 150 mA	-	-	1.25	V
I _R	reverse current	V _R = 25 V	-	-	30	nA
		V _R = 80 V	-	-	0.5	μΑ
		V_R = 25 V; T_j = 150 °C	-	-	30	μΑ
		V_R = 80 V; T_j = 150 °C	-	-	50	μΑ
C _d	diode capacitance	$f = 1 \text{ MHz}; V_R = 0 \text{ V}$				
	BAS16; BAS16H; BAS16J; BAS16L; BAS16T; BAS16VV; BAS16VY; BAS16W; BAS316		-	-	1.5	pF
	BAS516		-	-	1	pF
t _{rr}	reverse recovery time		[2] _	-	4	ns
V _{FR}	forward recovery voltage		[3]	-	1.75	V

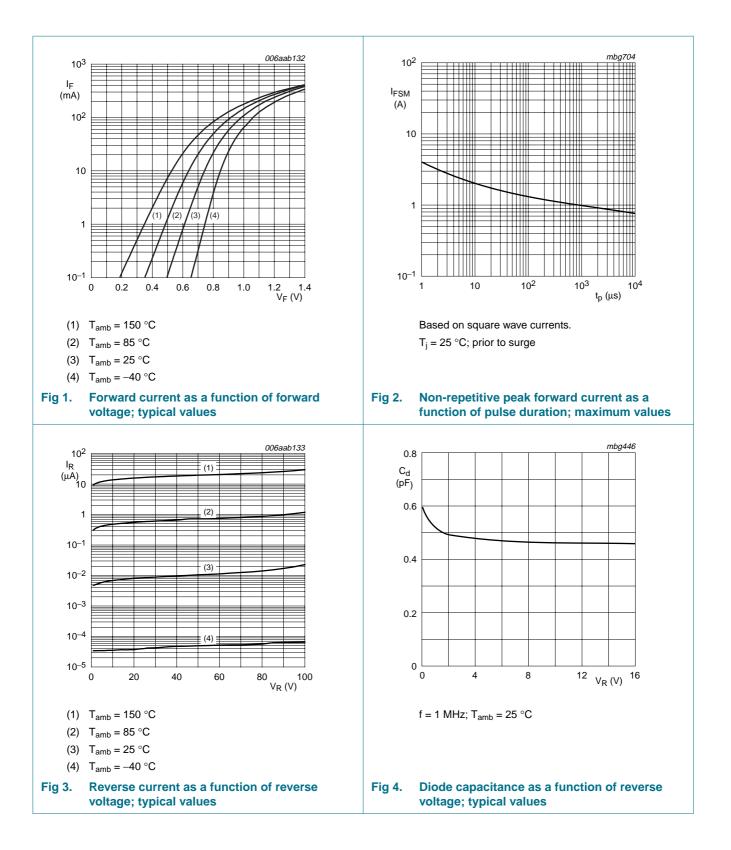
[1] Pulse test: $t_p \le 300 \ \mu s$; $\delta \le 0.02$.

[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

[3] When switched from $I_F = 10$ mA; $t_r = 20$ ns.

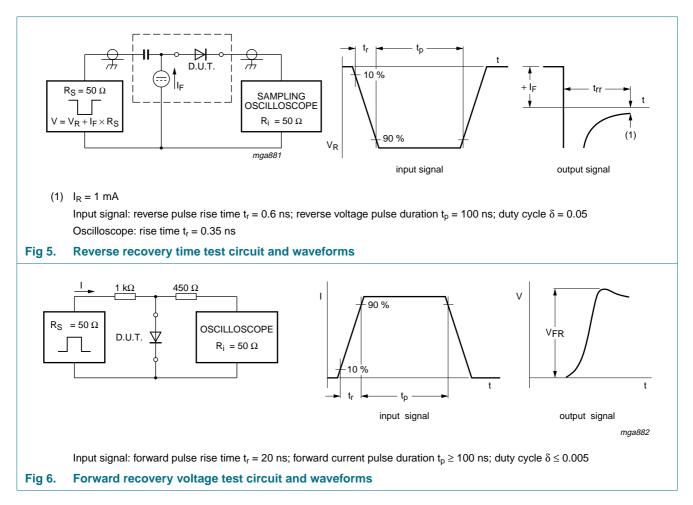
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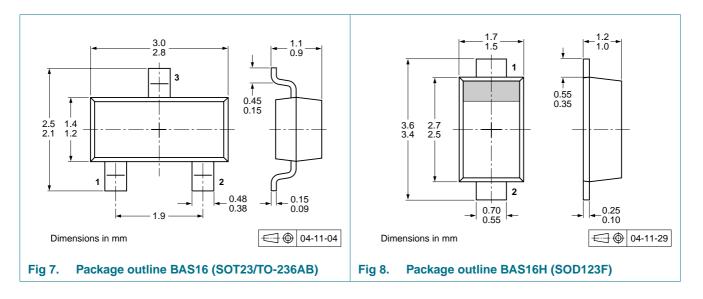


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8. Test information

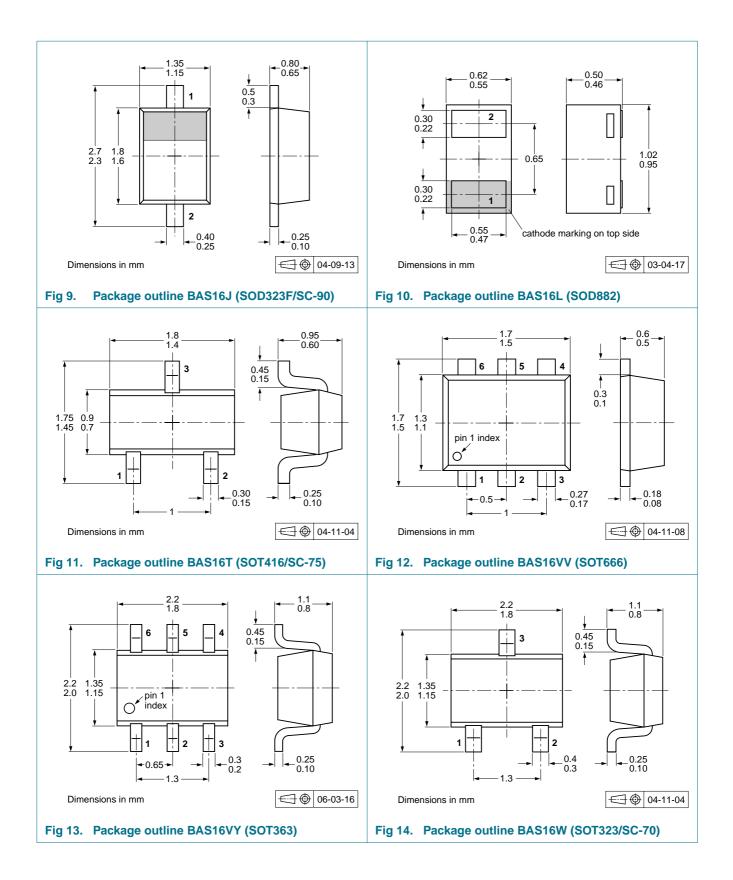


9. Package outline

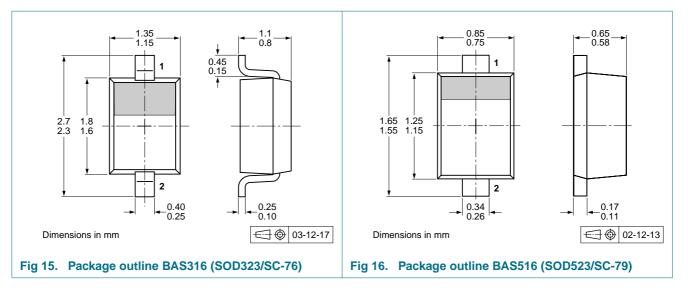


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High-speed switching diodes



10. Packing information

Table 9.Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description		Packing quantity			
				3000	4000	8000	10000
BAS16	SOT23	4 mm pitch, 8 mm tape and reel	Ĭ	-215	-	-	-235
BAS16H	SOD123F	4 mm pitch, 8 mm tape and reel		-115	-	-	-135
BAS16J	SOD323F	4 mm pitch, 8 mm tape and reel		-115	-	-	-135
BAS16L	SOD882	2 mm pitch, 8 mm tape and reel		-	-	-	-315
BAS16T	SOT416	4 mm pitch, 8 mm tape and reel		-115	-	-	-135
BAS16VV	SOT666	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-	-115	-	-
BAS16VY	SOT363	4 mm pitch, 8 mm tape and reel; T1	[2]	-115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	[3]	-125	-	-	-165
BAS16W	SOT323	4 mm pitch, 8 mm tape and reel		-115	-	-	-135
BAS316	SOD323	4 mm pitch, 8 mm tape and reel		-115	-	-	-135
BAS516	SOD523	2 mm pitch, 8 mm tape and reel		-	-	-315	-
		4 mm pitch, 8 mm tape and reel		-115	-	-	-135

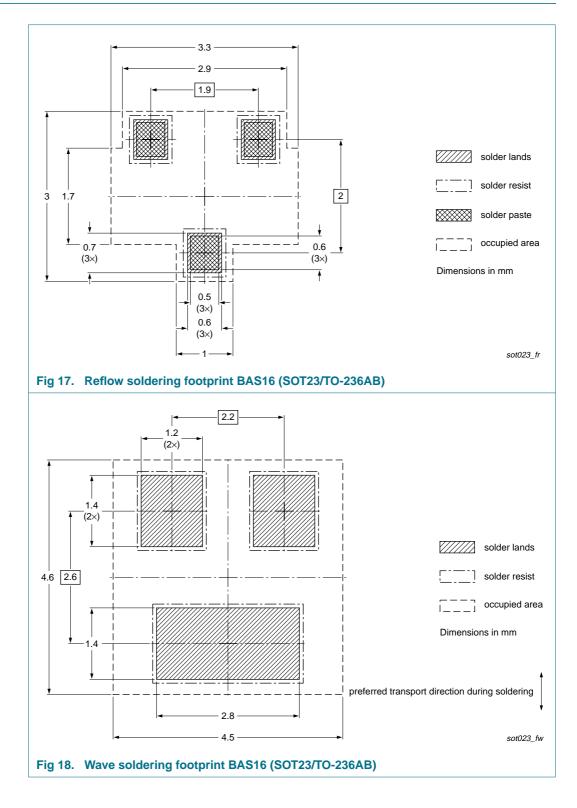
[1] For further information and the availability of packing methods, see Section 14.

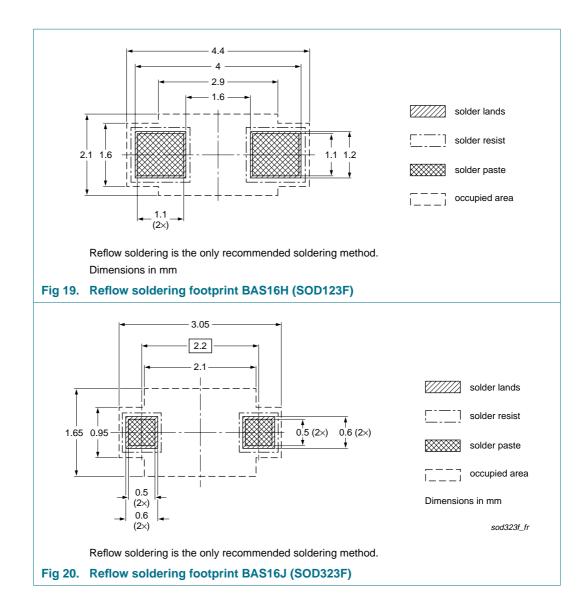
[2] T1: normal taping

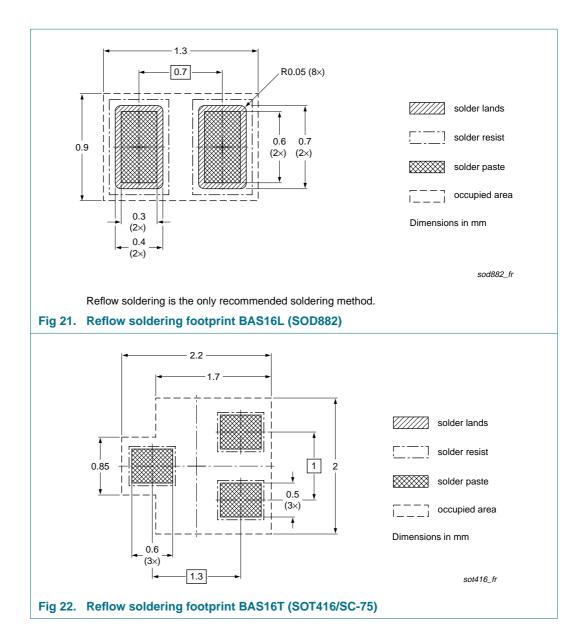
[3] T2: reverse taping

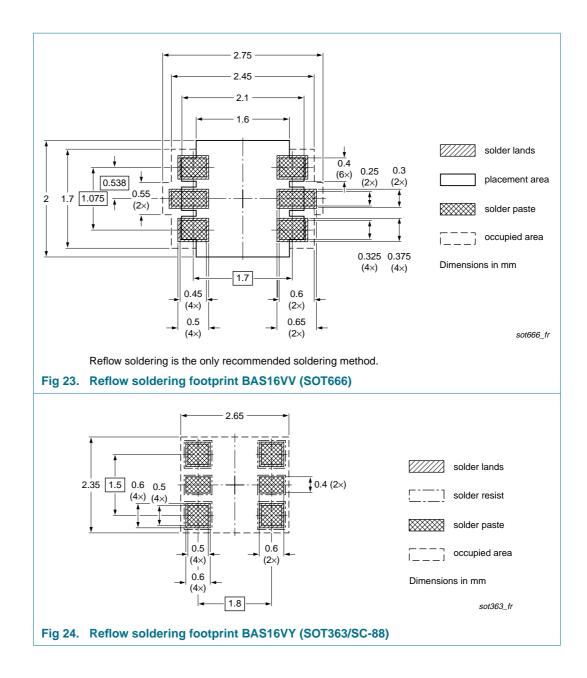
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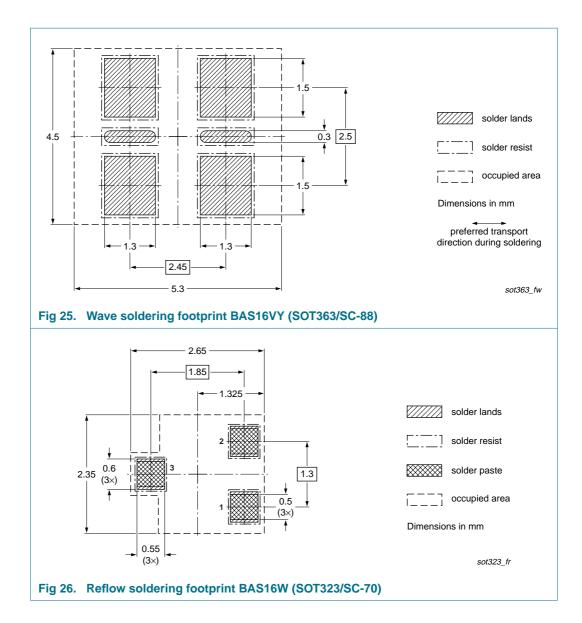
11. Soldering

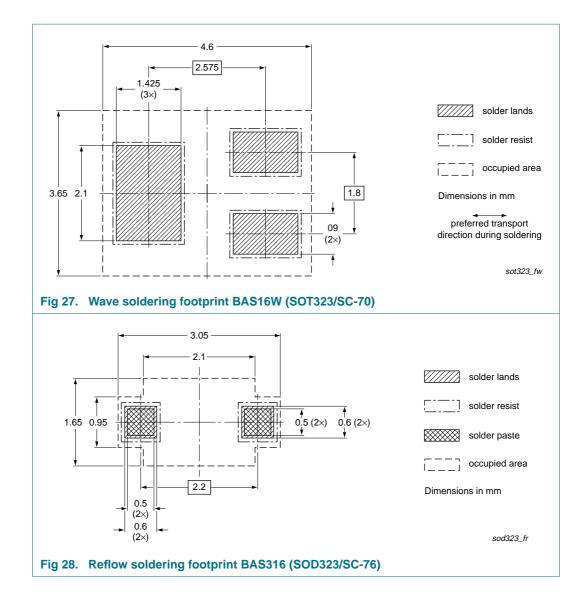


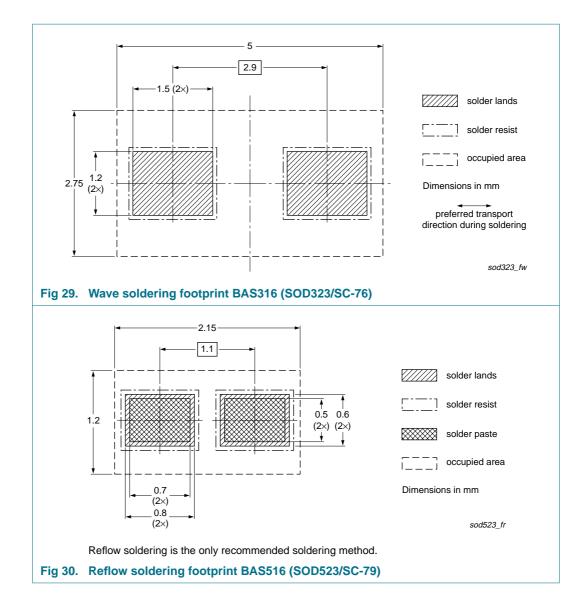












12. Revision history

Table 10. Revision histo	ory						
Document ID	Release date	Data sheet status	Change notice	Supersedes			
BAS16_SER_5	20080825	Product data sheet	-	BAS16_4 BAS16H_1 BAS16J_1 BAS16L_1 BAS16T_1 BAS16VV_BAS16VY_3 BAS16W_4 BAS316_4 BAS516_1			
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 						
	 Legal texts have been adapted to the new company name where appropriate. 						
	 <u>Table 5 "Marking codes</u>": marking code amended for BAS16W 						
	 <u>Table 6 "Limiting values"</u>: for BAS16, BAS16T, BAS16W and BAS516 change of V_{RRM} maximum value from 85 V to 100 V 						
	 <u>Table 6 "Limiting values</u>": for BAS16, BAS16L, BAS16T, BAS16W and BAS516 change of V_R maximum value from 75 V to 100 V 						
	• Table 8 "Characteristics": change of I_R condition V_R from 75 V to 80 V for $T_i = 25 \text{ °C}$						
	• Table 8 "Characteristics": change of I _R maximum value from 1.0 μ A to 0.5 μ A for V _R = 80 V and T _i = 25 °C						
	• Table 8 "Characteristics": change of I _R condition V _R from 75 V to 80 V for T _i = 150 °C						
	Section 13 "Legal information": updated						
BAS16_4	20011010	Product specification	-	BAS16_3			
BAS16H_1	20050415	Product data sheet	-	-			
BAS16J_1	20070308	Product data sheet	-	-			
BAS16L_1	20030623	Product specification	-	-			
BAS16T_1	19980120	Product specification	-	-			
BAS16VV_BAS16VY_3	20070420	Product data sheet	-	BAS16VV_BAS16VY_2			
BAS16W_4	10000500	Product specification	-	BAS16W_3			
DA310W_4	19990506	r roudor opcomoution		D/(010W_0			
BAS316_4	19990506 20040204	Product specification	-	BAS316_3			

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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15. Contents

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Date of release: 25 August 2008 Document identifier: BAS16_SER_5



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